L Number	Hits	Search Text	DB	Time stamp
3	3	diffusion adj region near6 "between" near6 isolation adj region and (mos or	USPAT; US-PGPUB;	2003/05/14
		mosfet).ti,ab,clm. and protection	EPO; JPO; DERWENT; IBM TDB	
4	0	(mos or mosfet).ti,ab,clm. and protection.ti,ab,clm. and separated near6 diffusion adj region near6 (isolation or	USPAT; US-PGPUB; EPO; JPO;	2003/05/14 14:00
_		field adj oxide or locos)	DERWENT; IBM_TDB	
5	0	("(mos or mosfet) near6 separated.ti,ab,clm.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14
6	577	(mos or mosfet) near6 separated.ti,ab,clm.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14 14:01
7	24	<pre>((mos or mosfet) near6 separated.ti,ab,clm.) and protection near2 (device or circuit)</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14 14:07
8	8	<pre>((mos or mosfet) near6 separated.ti,ab,clm.) and protection near2 (device or circuit) and (silicide or salicide)</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14 14:13
9	876	protection near2 (device or circuit) and (silicide or salicide)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14 14:15
10	24	(fox or locos) near6 diode and (mos or mosfet)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/14 14:22
11	8	(fox or locos) near6 diode and (mos or mosfet) and (silicide or salicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/14 14:32
12	0	array near2 lateral adj mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14 14:33
13	0	array near2 lateral adj mosfet and mosfet.ti,ab,clm.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/05/14 14:34
14	0	plurality near2 lateral adj mosfet.clm. and mosfet.ti,ab,clm.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/05/14 14:35
			DERWENT; IBM TDB	
15	407	plurality near2 mosfet.clm. and mosfet.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/14 14:35

				T
16	1	plurality near2 mosfet.clm. and	USPAT;	2003/05/14
		mosfet.ti,ab,clm. and silicide and fox	US-PGPUB;	14:54
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	2	silicide near6 advantage\$3 near6 smooth	USPAT;	2003/05/14
			US-PGPUB;	15:53
			EPO; JPO;	
			DERWENT;	
10			IBM_TDB	2002/05/14
18	0	"on the same substrate" near6 plurality near6 mosfet	USPAT;	2003/05/14
		neare mostet	US-PGPUB;	15:55
			EPO; JPO;	
			DERWENT;	1
19	0	"insulated from other MOSFETs"	IBM_TDB USPAT;	2003/05/14
19	١	Insuraced from other mosters		
			US-PGPUB;	15:55
			EPO; JPO;	
			DERWENT;	
20	18	tfo and cmos	IBM_TDB USPAT;	2002/05/14
۷.	18	CIO and Chios	i i	2003/05/14 17:44
			US-PGPUB;	1,,44
			EPO; JPO;	
			DERWENT;	
21	2	jp-06224376\$-\$.did.	IBM_TDB USPAT;	2003/05/14
21]p-002243765-5.did.	US-PGPUB;	19:17
	,		EPO; JPO;	19:17
			DERWENT;	
			IBM TDB	
22	59	physical adj vapor adj deposition near2	USPAT;	2003/05/14
42		electrode	US-PGPUB;	20:3703714
		61661646	EPO; JPO;	20.12
			DERWENT;	
			IBM TDB	
23	5	866782.ap.	USPAT;	2003/05/14
			US-PGPUB;	20:14
			EPO; JPO;	
*			DERWENT;	
			IBM_TDB	
24	5	873370.ap.	USPAT;	2003/05/14
		•	US-PGPUB;	20:17
			EPO; JPO;	
	ļ		DERWENT;	
	1		IBM_TDB	
25	2	jp-07273197\$-\$.did.	USPAT;	2003/05/14
			US-PGPUB;	20:18
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
26	2	jp-07106570\$-\$.did.	USPAT;	2003/05/14
			US-PGPUB;	20:18
			EPO; JPO;	
	l .		DERWENT;	
			IBM_TDB	
27	2	jp-07094595\$-\$.did.	USPAT;	2003/05/14
			US-PGPUB;	20:42
]		EPO; JPO;	
			DERWENT;	
20	1	//857440418) /850007748)	IBM_TDB	2002/05/24
28	2	(("5744841") or ("5920774")).PN.	USPAT	2003/05/14
	_	(Manada ada Mara) may	TIOD S.T.	20:42
_	0	("salicide").PN.	USPAT;	2003/05/14
			US-PGPUB;	13:36
	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	

_	2475	salicide	USPAT;	2002/03/05
			US-PGPUB;	17:08
			EPO; JPO;	1
			DERWENT;	
			IBM_TDB	
_	431	salicide.ti.	USPAT;	2002/03/05
			US-PGPUB;	17:08
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	229	(257/173).CCLS.	USPAT;	2002/10/04
	223	(237/173):00113:	US-PGPUB	11:04
	322	(257/339).CCLS.		2002/10/04
-	322	(257/359).0015.	USPAT;	1
	725	(257/255) agra	US-PGPUB	11:04
_	725	(257/355).CCLS.	USPAT;	2002/10/04
			US-PGPUB	11:04
-	1186	((257/173).CCLS.) or ((257/339).CCLS.) or	USPAT;	2002/10/04
		((257/355).CCLS.)	US-PGPUB;	12:05
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	18	(((257/173).CCLS.) or ((257/339).CCLS.)	USPAT;	2002/10/04
		or ((257/355).CCLS.)) and (mos or mosfet	US-PGPUB;	13:58
	1	or nmos or nmosfet or pmos or pmosfet or	EPO; JPO;	
		cmos or cmosfet) and protect\$3 and	DERWENT;	
		silicide and zener	IBM TDB	į
_	18		USPAT;	2002/10/04
1	"	US-6268639-\$ or US-6175139-\$ or	US-PGPUB	13:29
			05-16108	13.29
		US-6121665-\$ or US-5939767-\$ or		
		US-5910675-\$ or US-5708288-\$ or		
		US-5683918-\$ or US-5623387-\$ or		
		US-5543650-\$ or US-5229633-\$ or		
		US-5166089-\$ or US-5128730-\$ or		
	1	US-4509089-\$ or US-6365941-\$).did. or		
1		(US-20020096722-\$ or		
		US-20020030231-\$).did.		
-	132		USPAT;	2002/10/04
	l	or ((257/355).CCLS.)) and (mos or mosfet	US-PGPUB;	14:07
	1	or nmos or nmosfet or pmos or pmosfet or	EPO; JPO;	
	1	cmos or cmosfet) and zener	DERWENT;	
	[<u>'</u>	IBM TDB	
_	30	((257/288).CCLS.) and second near3	USPAT;	2002/10/04
		diffusion	US-PGPUB;	14:16
			EPO; JPO;	[]
			DERWENT;	
1			IBM TDB	1
_	7	((257/288).CCLS.) and double-diffused	USPAT;	2002/10/04
1	1 '	(\25,7200).ccbs./ and doubte-diffused	US-PGPUB;	14:17
				13.1/
1 .			EPO; JPO;	
`			DERWENT;	1
		//057/000\ ggtg \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	IBM_TDB	1 0000 /70 /01
-	11	((257/288).CCLS.) and double adj diffused	USPAT;	2002/10/04
1			US-PGPUB;	14:18
1			EPO; JPO;	
1			DERWENT;	į l
1			IBM_TDB	1
-	788	(257/288).CCLS.	USPAT;	2002/10/04
			US-PGPUB;	14:31
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	8	(US-6025628-\$ or US-6307224-\$ or	USPAT;	2002/10/04
1		US-4509089-\$ or US-5166089-\$ or	US-PGPUB;	19:04
		US-6268639-\$ or US-5623387-\$).did. or	JPO	-5.0.
		(US-20020030231-\$).did. or	550	
1				1
1	_	(JP-06204475-\$).did.	HCDAE	2002/10/04
-	8	((US-6025628-\$ or US-6307224-\$ or	USPAT;	2002/10/04
		US-4509089-\$ or US-5166089-\$ or	US-PGPUB;	19:18
		US-6268639-\$ or US-5623387-\$).did. or	EPO; JPO;	
		(US-20020030231-\$).did. or	DERWENT;	1
1	l .	(JP-06204475-\$).did.)	IBM_TDB	

Search History 5/14/03 9:30:42 PM Page 3

-	463	1	USPAT;	2002/10/04
		esd	US-PGPUB;	19:19
			EPO; JPO;	
			DERWENT;	
	0.00		IBM_TDB	
-	268		USPAT;	2002/10/04
		esd and 257/\$6.ccls.	US-PGPUB;	19:19
			EPO; JPO;	
			DERWENT;	
	110		IBM_TDB	
-	112		USPAT;	2002/10/04
		esd and 257/\$6.ccls.) and well near4	US-PGPUB;	19:20
		protect\$3	EPO; JPO;	
			DERWENT;	
_	37	/11	IBM_TDB	
_	37	1 ,	USPAT;	2002/10/04
		esd and 257/\$6.ccls.) and well near4	US-PGPUB;	19:21
		protect\$3.ti,ab,clm.	EPO; JPO;	
			DERWENT;	
_	1,2	(IBM_TDB	2000/10/04
_	12	• • • • • • • • • • • • • • • • • • •	USPAT;	2002/10/04
		esd and 257/\$6.ccls.) and well near4	US-PGPUB;	19:22
		protect\$3.ti,ab,clm. and (mos or	EPO; JPO;	
		mosfet).ti,ab,clm.	DERWENT;	
		/#4226490#\ px	IBM_TDB	2002/12/26
-	4	("4336489").PN.	USPAT;	2002/10/06
			US-PGPUB;	10:34
			EPO; JPO;	
			DERWENT;	
		070701074 A 14 1	IBM_TDB	0000 (05 (14
-	2	jp-07273197\$-\$.did.	USPAT;	2003/05/14
			US-PGPUB;	09:42
			EPO; JPO;	
			DERWENT;	
	2	in 071065706 6 444	IBM_TDB	2002/05/14
-	2	jp-07106570\$-\$.did.	USPAT;	2003/05/14
			US-PGPUB;	09:33
]			EPO; JPO;	
			DERWENT;	
_	2	jp-07094995\$-\$.did.	IBM_TDB USPAT;	2003/05/14
1	_	Jp 0/0949930-4.drd.	US-PGPUB;	09:56
			EPO; JPO;	09.56
			DERWENT;	
			IBM TDB	
_	2	jp-07094595\$-\$.did.	USPAT;	2003/05/14
		Jp 0/0510504 4.414.	US-PGPUB;	09:47
			EPO; JPO;	""
			DERWENT;	
			IBM TDB	
_	1	jp-05136086\$-\$.did.	USPAT;	2003/05/14
	1	J	US-PGPUB;	09:51
			EPO; JPO;	33.31
			DERWENT;	
			IBM TDB	
l -	2	jp-03234062\$-\$.did.	USPAT;	2003/05/14
		JF TODO TO OUT TOUR	US-PGPUB;	09:54
			EPO; JPO;	""
			DERWENT;	
			IBM TDB	
-	2	jp-02271673\$-\$.did.	USPAT;	2003/05/14
		Jr Trouban	US-PGPUB;	11:33
			EPO; JPO;	-1.55
			DERWENT;	
1			IBM TDB	
_	11	jp-07273197\$-\$.did. or	USPAT;	2003/05/14
	**	jp-07106570\$-\$.did. or	US-PGPUB;	09:58
		jp-071003703-3.did. or jp-07094995\$-\$.did. or	EPO; JPO;	""
		jp-07094995\$-\$.did. or	DERWENT;	
		jp-070943937-3.did. or jp-05136086\$-\$.did. or	IBM TDB	
		jp-031360607-3.did.	1511-100	
		INE COURT TOWARD.		

_	2012	((257/173) or (257/339) or	USPAT;	2003/05/14
		(257/355)).CCLS.	US-PGPUB; EPO; JPO;	12:12
			DERWENT;	
			IBM TDB	
_	14	(((257/173) or (257/339) or	USPAT;	2003/05/14
		(257/355)).CCLS.) and salicide and (MOS	US-PGPUB;	11:38
		or MOSFET or CMOS or CMOSFET or NMOS or	EPO; JPO;	
		PMOS or NMOSFET or PMOSFET) and hot adj	DERWENT;	
_	9	(salicide and (MOS or MOSFET or CMOS or	IBM_TDB USPAT;	2003/05/14
	_	CMOSFET or NMOS or PMOS or NMOSFET or	US-PGPUB;	11:39
		PMOSFET) and hot adj spot) not	EPO; JPO;	
		((((257/173) or (257/339) or	DERWENT;	
		(257/355)).CCLS.) and salicide and (MOS	IBM_TDB	
		or MOSFET or CMOS or CMOSFET or NMOS or PMOS or NMOSFET or PMOSFET) and hot adj		
		spot)		
_	23	salicide and (MOS or MOSFET or CMOS or	USPAT;	2003/05/14
		CMOSFET or NMOS or PMOS or NMOSFET or	US-PGPUB;	11:42
		PMOSFET) and hot adj spot	EPO; JPO;	
			DERWENT;	
_	1	(((257/173) or (257/339) or	IBM_TDB USPAT;	2003/05/14
1-		(((257/173) of (257/339) of (257/355)).CCLS.) and salicide and (fox	US-PGPUB;	12:15
		of field adj oxide or locos) and lateral	EPO; JPO;	12.13
		adj bipolar adj transistor and (mos or	DERWENT;	
		mosfet or cmos or cmosfet or nmos or	IBM_TDB	
		nmosfet or pmos or pmosfet or field adj		
		effect adj transistor) and protection		
_	9	near3 (circuit or device) and zener (((257/173) or (257/339) or	USPAT;	2003/05/14
		((257/355)).CCLS.) and salicide and (mos	US-PGPUB;	12:22
		or mosfet or cmos or cmosfet or nmos or	EPO; JPO;	
		nmosfet or pmos or pmosfet or field adj	DERWENT;	
		effect adj transistor or igfet or	IBM_TDB	
		insulated adj gate adj field adj effect adj transistor) and protection near3		
		(circuit or device) and zener		
-	14		USPAT;	2003/05/14
		(257/355)).CCLS.) and salicide and (mos	US-PGPUB;	12:24
		or mosfet or cmos or cmosfet or nmos or	EPO; JPO;	
		nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or	DERWENT;	
		insulated adj gate adj field adj effect	IBM_TDB	
		adj transistor) and hot adj spot		
-	12	((((257/173) or (257/339) or	USPAT;	2003/05/14
		(257/355)).CCLS.) and salicide and (mos	US-PGPUB;	12:24
		or mosfet or cmos or cmosfet or nmos or	EPO; JPO;	
		nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or	DERWENT; IBM TDB	
		insulated adj gate adj field adj effect	TEL TOP	
		adj transistor) and hot adj spot) not		
		((((257/173) or (257/339) or		
		(257/355)).CCLS.) and salicide and (mos		
		or mosfet or cmos or cmosfet or nmos or		
		nmosfet or pmos or pmosfet or field adj effect adj transistor or igfet or		
		insulated adj gate adj field adj effect		
		adj transistor) and protection near3		
		(circuit or device) and zener)		
		·		· · · · · · · · · · · · · · · · · · ·